

**IN THE CLAIMS:**

**Amendments to the claims:**

This listing of claims will replace all prior versions, and listings of claims in the application.

**Listing of claims:**

- 1-20. (Canceled)
21. (Previously presented) An EMI/RFI shielding device comprising:  
a shaped polymer substrate comprised of a recycled metallized polymer substrate,  
wherein the shaped polymer substrate is substantially conductive; and  
a conductive material on at least one surface of the shaped polymer substrate.
22. (Previously presented) The EMI/RFI shielding device of claim 21  
wherein the recycled metallized polymer substrate comprises a reground and re-extruded  
metallized thermoform.
23. (Currently amended) The EMI/RFI shielding device of claim 21 wherein  
the metallized thermoform shaped polymer substrate comprises polyvinyl chloride,  
polycarbonate, polybutylene terephthalate, or polyethylene terephthalate glycol.
24. (Previously presented) The EMI/RFI shielding device of claim 21  
wherein the conductive material has a thickness between 1.0 micron and 50.0 microns.
25. (Previously presented) The EMI/RFI shielding device of claim 21  
wherein the conductive material comprises aluminum.

26. (Previously presented) The EMI/RFI shielding device of claim 21 wherein the conductive material comprises a substantially uniform thickness over at least one surface of the shaped polymer substrate.

27. (Previously presented) The EMI/RFI shielding device of claim 21 wherein the shaped polymer substrate has a thickness between 0.006 inches to 0.100 inches.

28. (Previously presented) The EMI/RFI shielding device of claim 21 wherein the shaped polymer substrate comprises:

a first surface;

a plurality of sidewalls that comprise a first end and a second end, wherein a first end of each of the sidewalls are coupled to the first surface, wherein the sidewalls extend at an angle from the first surface, wherein the first surface and sidewalls define an enclosure portion; and

a peripheral flange coupled to the second end of the sidewalls that extends around the enclosure portion.

29. (Previously presented) An EMI/RFI shield comprising:

a thermoformed thin-walled shape formed of a recycled metallized polymeric material, wherein the thermoformed thin-walled shape comprises an inner surface, an outer surface and edges; and

a conductive material deposited on at least one of the inner surface and outer surface, wherein the conductive coating comprises a substantially even thickness between 1 micron to 50 microns.

30. (Previously presented) The EMI/RFI shield of claim 29 wherein the conductive material comprises vacuum deposited aluminum.

31. (Previously presented) The EMI/RFI shield of claim 29 wherein the recycled metallized polymeric material comprises a reground and re-extruded metal layer and a polymeric material.

32. (Previously presented) The EMI/RFI shield of claim 29 wherein the polymeric material comprises polyvinyl chloride, polycarbonate, polybutylene terephthalate, or polyethylene terephthalate glycol.

33. (Previously presented) The EMI/RFI shield of claim 29 wherein the thermoformed thin-walled shape has a thickness between 0.006 inches to 0.100 inches.

34. (Previously presented) The EMI/RFI shield of claim 29 wherein the thermoformed thin-walled shape comprises:

a first surface;

a plurality of sidewalls that comprise a first end and a second end, wherein a first end is coupled to the first surface, wherein the sidewalls extend at an angle from the first surface, wherein the first surface and sidewalls define an enclosure portion; and

a peripheral flange coupled to the second end of the sidewalls that extends around the enclosure portion.

35. (Withdrawn) A method of manufacturing an EMI/RFI shield, the method comprising:

processing a metallized polymeric shape;

extruding the processed metallized polymeric shape into a sheet;

shaping the sheet to form a thin walled shape;

applying a conductive layer onto at least one surface of the thin-walled shape.

36. (Withdrawn) The method of claim 35 wherein processing comprises shredding and grinding the metallized polymeric shape.

37. (Withdrawn) The method of claim 35 wherein applying a conductive layer comprise vacuum metallizing a metal onto the thin-walled shape.

38 (Withdrawn) The method of claim 37 wherein the conductive layer has a substantially uniform thickness between 1.0 micron and 50.0 microns.

39 (Withdrawn) The method of claim 35 wherein shaping comprises:  
forming a first surface;  
forming a plurality of sidewalls that have a first end coupled to the first surface,  
wherein the plurality of sidewalls extend at an angle away from the first surface; and  
forming a peripheral flange on a second end of the plurality of sidewalls,  
wherein the first surface and the plurality of sidewalls define an enclosure.

40. (Withdrawn) The method of claim 35 wherein applying a conductive layer comprises thermal evaporating, painting, cathode sputtering, ion plating, electroless plating, electron beam, cathodic-arc, or vacuum thermal spraying.

41. (Withdrawn) The method of claim 35 wherein applying comprises applying the conductive layer to a first and second surface of the thin-walled shape.

42. (Withdrawn) The method of claim 35 wherein applying comprises applying the conductive layer to only one surface of the thin-walled shape.

43. (Withdrawn) The method of claim 35 wherein applying the conductive layer is carried out after shaping.

44. (Withdrawn) The method of claim 35 wherein applying the conductive layer is carried out before shaping.

45. (Withdrawn) The method of claim 35 wherein shaping comprises thermoforming the sheet.

46. (Previously presented) The EMI/RFI shielding device of claim 21 further comprising grinding and re-extruding a metal material along with the polymer substrate.

47. (Canceled)

48. (Withdrawn) A method of manufacturing an EMI/RFI shield, the method comprising:

grinding a used metallized polymeric shape;  
extruding the ground metallized polymeric shape into a sheet;  
shaping the sheet to form a thin walled EMI/RFI shield that defines an enclosure.

49. (New) The EMI/RFI shielding device of claim 21 wherein the conductive material comprises copper.

50. (New) The EMI/RFI shielding device of claim 21 wherein the conductive material comprises nickel.

51. (New) The EMI/RFI shield of claim 29 wherein the conductive material comprises vacuum deposited copper.

52. (New) The EMI/RFI shield of claim 29 wherein the conductive material comprises vacuum deposited nickel.